



N 沟道增强型场效应晶体管
N-CHANNEL MOSFET
FHA150N06C

主要参数 MAIN CHARACTERISTICS

ID	150 A
VDSS	55 V
Rdson-typ (@Vgs=10V)	7.2 mΩ
Qg-typ	118nC

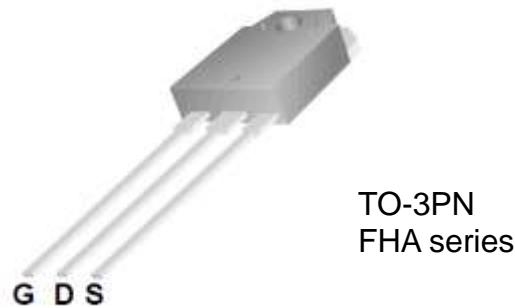
用途 APPLICATIONS

12V逆变电源	Power management for 12V inverter systems
同步整流	Synchronous Rectification

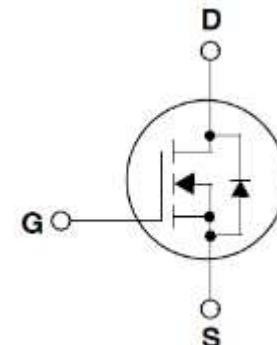
产品特性 FEATURES

低栅极电荷	Low gate charge
低 Crss (典型值 850pF)	Low Crss (typical 850pF)
开关速度快	Fast switching
100%经过雪崩测试	100% avalanche tested
高抗 dv/dt 能力	Improved dv/dt capability
RoHS 产品	RoHS product
平面工艺	Plane process

封装形式 Package



等效电路 Equivalent Circuit



绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
		FHA150N06C	
最高漏极—源极直流电压 Drain-Source Voltage	VDS	55	V
连续漏极电流* Drain Current -continuous *	Id (Tc=25°C)	150	A
	Id (Tc=100°C)	105	A
最大脉冲漏极电流 (注 1) Drain Current – pulse (note 1)	Idm	450	A
最高栅源电压 Gate-Source Voltage	VGS	±20	V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	EAS	1500	mJ
雪崩电流 (注 1) Avalanche Current (note 1)	IAR	25	A
重复雪崩能量 (注 1) Repetitive Avalanche Current (note 1)	EAR	20	mJ
二极管反向恢复最大电压变化速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	5.0	V/ns
耗散功率 Power Dissipation	PD (TC=25°C)	290	W
	-Derate above 25°C	1.69	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	TJ, TSTG	-55~+175	°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	TL	300	°C

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature

电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units	
关态特性 Off -Characteristics							
漏一源击穿电压 Drain-Source Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	55	-	-	V	
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /Δ TJ	I _D =250μA, referenced to 25°C	-	0.055	-	V/°C	
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =55V, V _{GS} =0V, T _C =25°C	-	-	1	μA	
		V _{DS} =44V, T _C =125°C	-	-	100	μA	
栅极体漏电流 Gate-body leakage current	I _{GSS} (F/R)	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA	
通态特性 On-Characteristics							
阈值电压 Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	2.0	3.0	4.0	V	
静态导通电阻 Static Drain-Source On-Resistance	R _{Ds(ON)}	V _{GS} =10V , I _D =40A	-	7.2	11.5	mΩ	
正向跨导 Forward Transconductance	g _{fs}	V _{DS} = 20V, I _D =40A (note 4)	40	-	-	S	
动态特性 Dynamic Characteristics							
栅电阻 Gate Resistance	R _g	f=1.0MHz, V _{DS} OPEN	-	1.7	-	Ω	
输入电容 Input capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	3000	-	pF	
输出电容 Output capacitance	C _{oss}		-	2100	-		
反向传输电容 Reverse transfer capacitance	C _{rss}		-	850	-		
开关特性 Switching Characteristics							
延迟时间 Turn-On delay time	t _{d(on)}	V _{DS} =30V, I _D =75A, R _G =4.5Ω V _{GS} =10V (note 4, 5)	-	14	-	ns	
上升时间 Turn-On rise time	t _r		-	101	-	ns	
延迟时间 Turn-Off delay time	t _{d(off)}		-	50	-	ns	
下降时间 Turn-Off Fall time	t _f		-	65	-	ns	
栅极电荷总量 Total Gate Charge	Q _g	V _{DS} =30V , I _D =75A , V _{GS} =10V (note 4, 5)	-	118	-	nC	
栅一源电荷 Gate-Source charge	Q _{gs}		-	30	-	nC	
栅一漏电荷 Gate-Drain charge	Q _{gd}		-	55	-	nC	
漏一源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings							
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	I _s		-	-	150	A	
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}		-	-	450	A	
正向压降 Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _s =62A	-	0.9	1.3	V	
反向恢复时间 Reverse recovery time	t _{rr}	V _{GS} =0V, I _s =62A ,dI _F /dt=100A/μs (note 4)	-	69	-	ns	
反向恢复电荷 Reverse recovery charge	Q _{rr}		-	143	-	nC	

热特性 THERMAL CHARACTERISTIC

项目 Parameter	符号 Symbol	最大值 Max	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	R _{th(j-c)}	0.31	°C/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	R _{th(j-A)}	40	°C/W

注释:

- 1: 脉冲宽度由最高结温限制
- 2: L=1mH, I_{AS}=25A, V_{DD}=44V, R_G=25 Ω, 起始结温 T_J=25°C
- 3: I_{SD} ≤ 150A, di/dt ≤ 300A/μs, V_{DD} ≤ BV_{DSS}, 起始结温 T_J=25°C
- 4: 脉冲测试: 脉冲宽度 ≤ 300μs, 占空比 ≤ 2%
- 5: 基本与工作温度无关

Notes:

- 1: Pulse width limited by maximum junction temperature
- 2: L=1mH, I_{AS}=25A, V_{DD}=44V, R_G=25 Ω, Starting T_J=25°C
- 3: I_{SD} ≤ 150A, di/dt ≤ 300A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J=25°C
- 4: Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
- 5: Essentially independent of operating temperature

特性曲线

Typical Characteristics

Fig. 1. Output Characteristics

@ 25°C

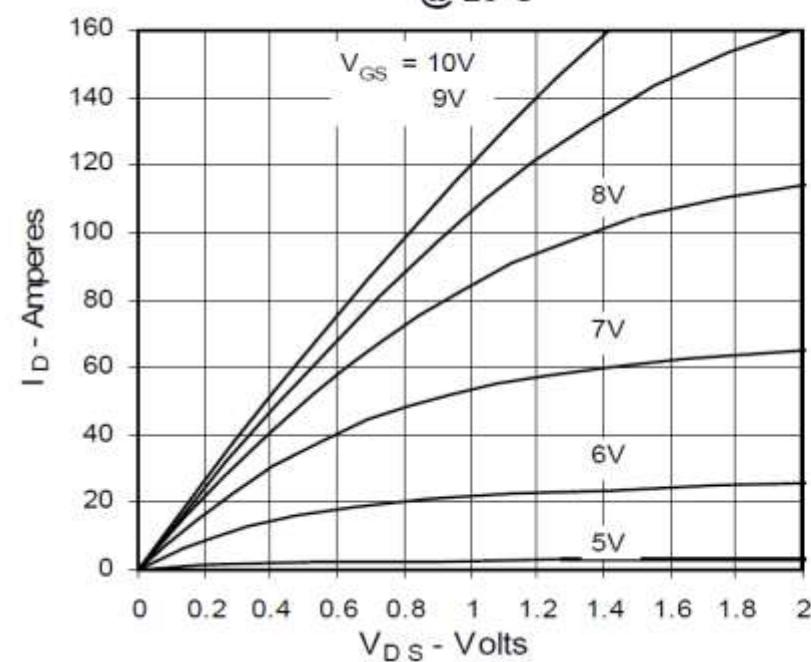


Fig. 2. Extended Output Characteristics

@ 25°C

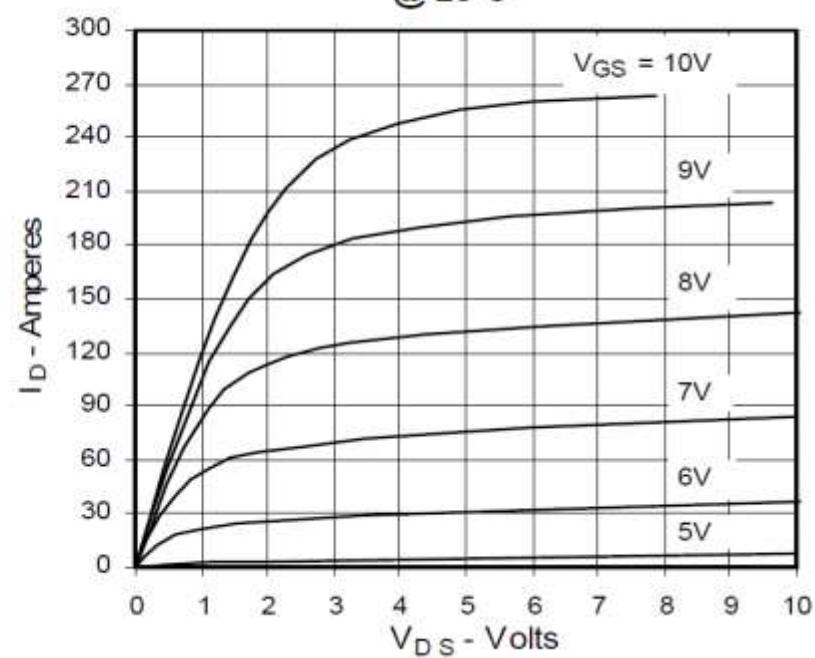


Fig. 3. Output Characteristics

@ 150°C

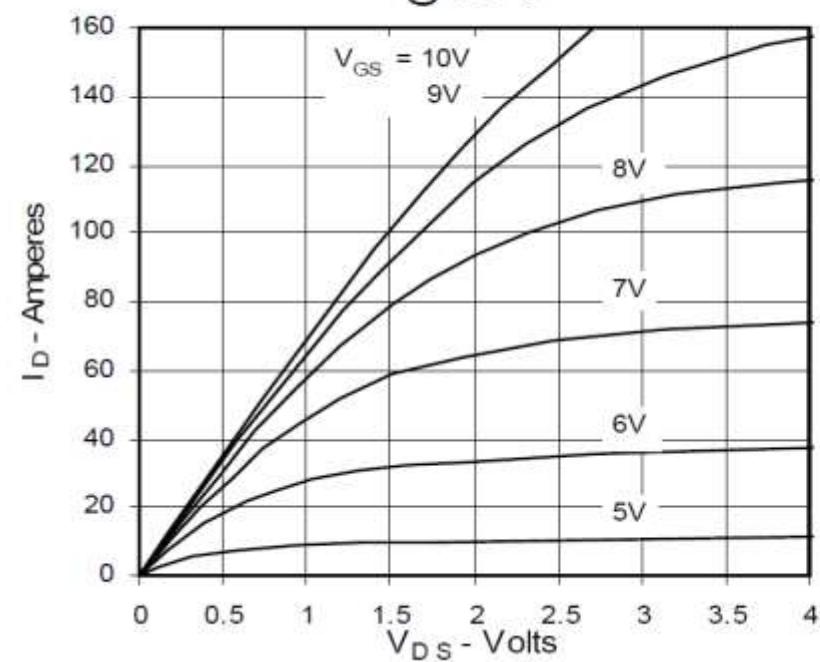


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

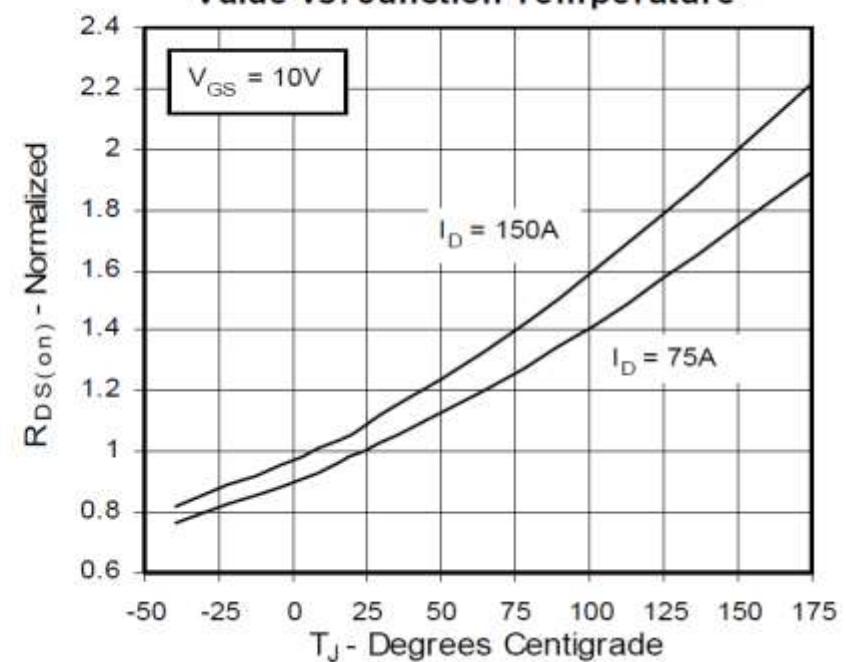


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Drain Current

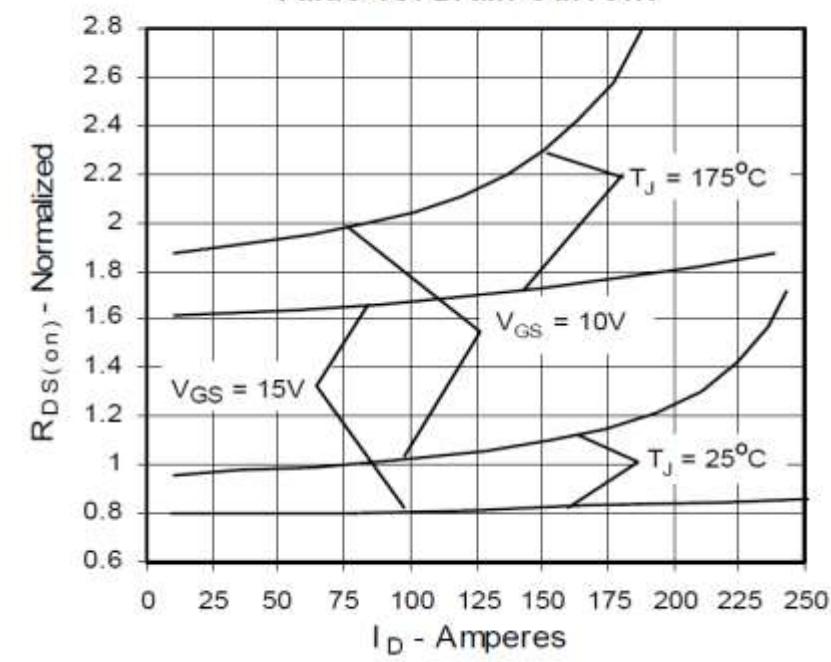


Fig. 6. Drain Current vs. Case Temperature

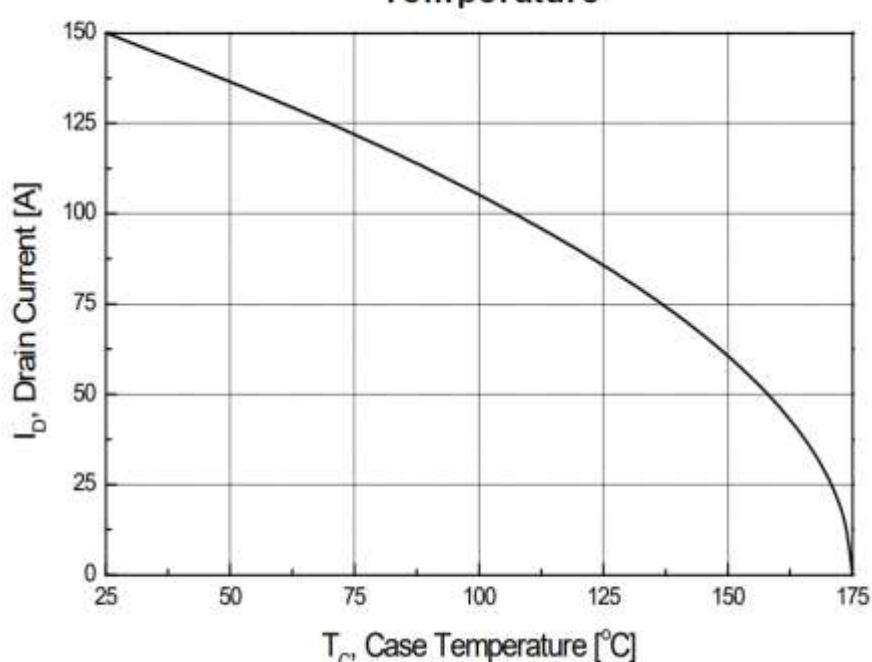


Fig. 7. Input Admittance

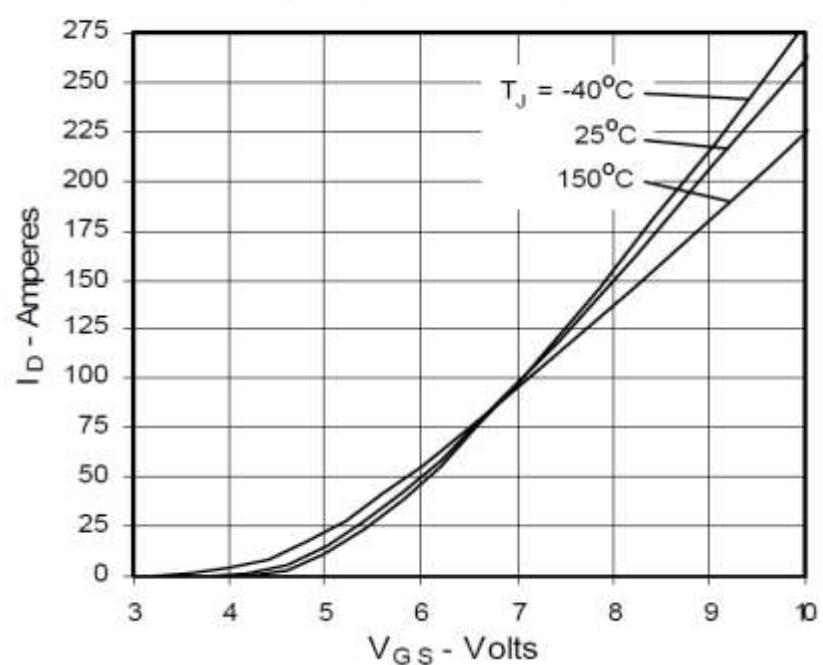


Fig. 8. Transconductance

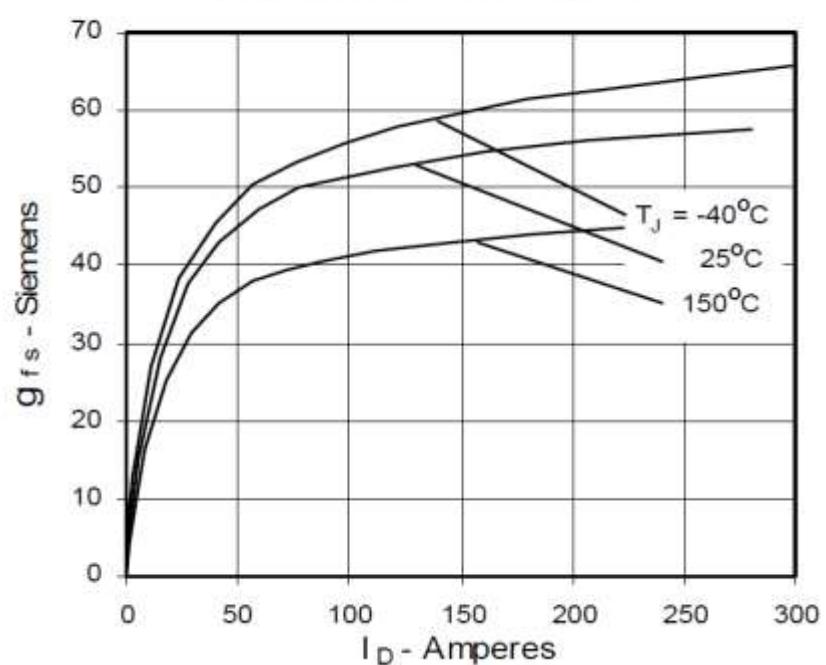


Fig. 9. Source Current vs. Source-To-Drain Voltage

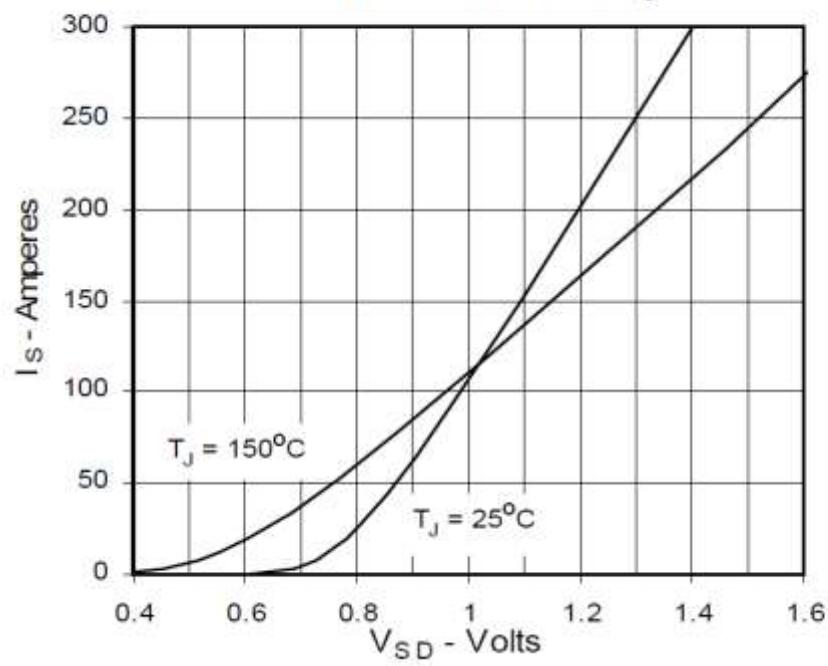


Fig. 10. Gate Charge

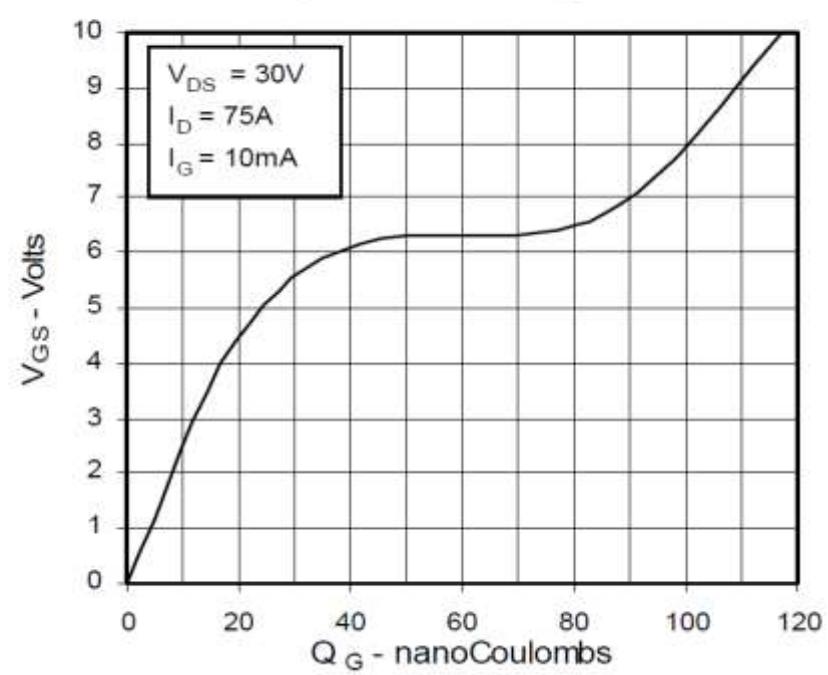


Fig. 11. Capacitance

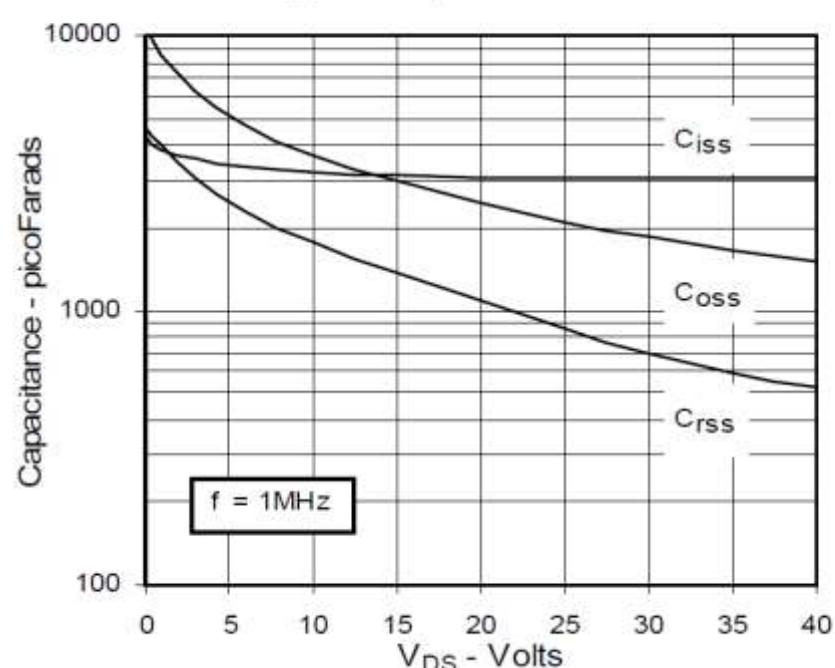


Fig. 12. Forward-Bias Safe Operating Area

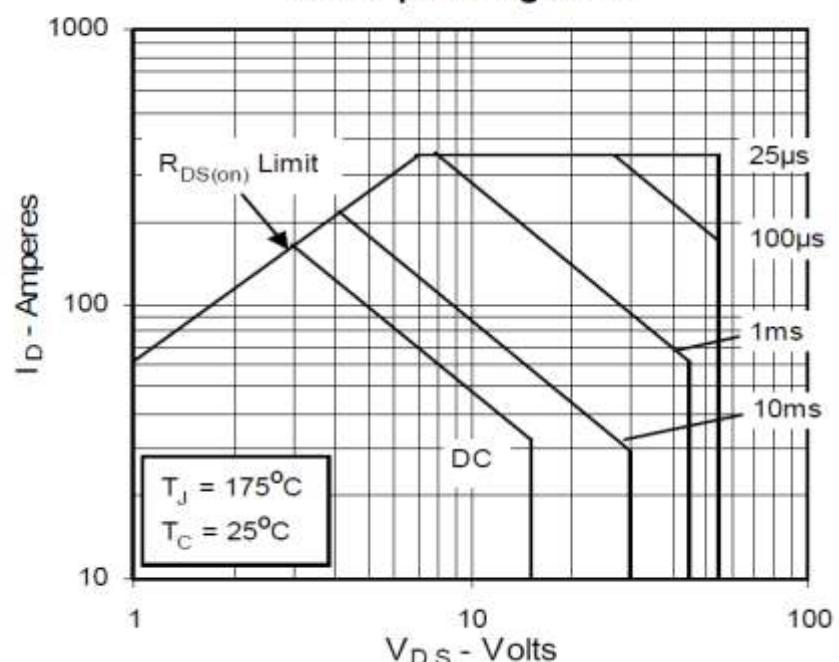
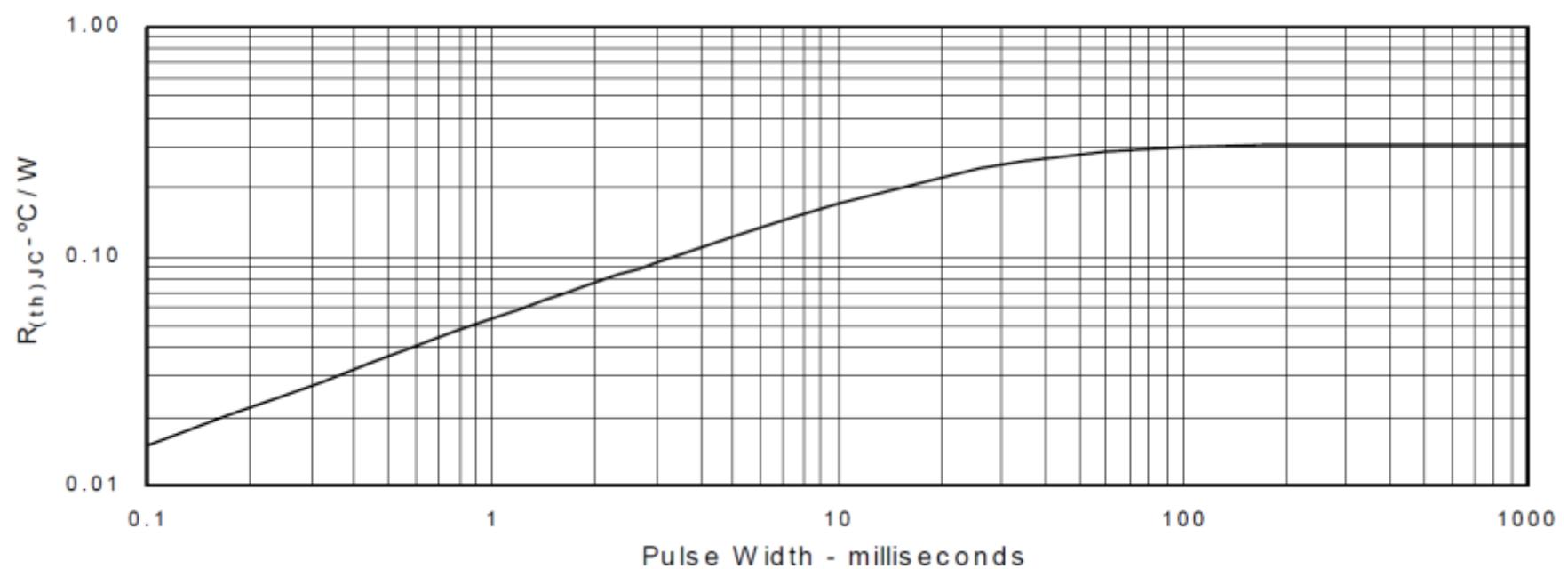
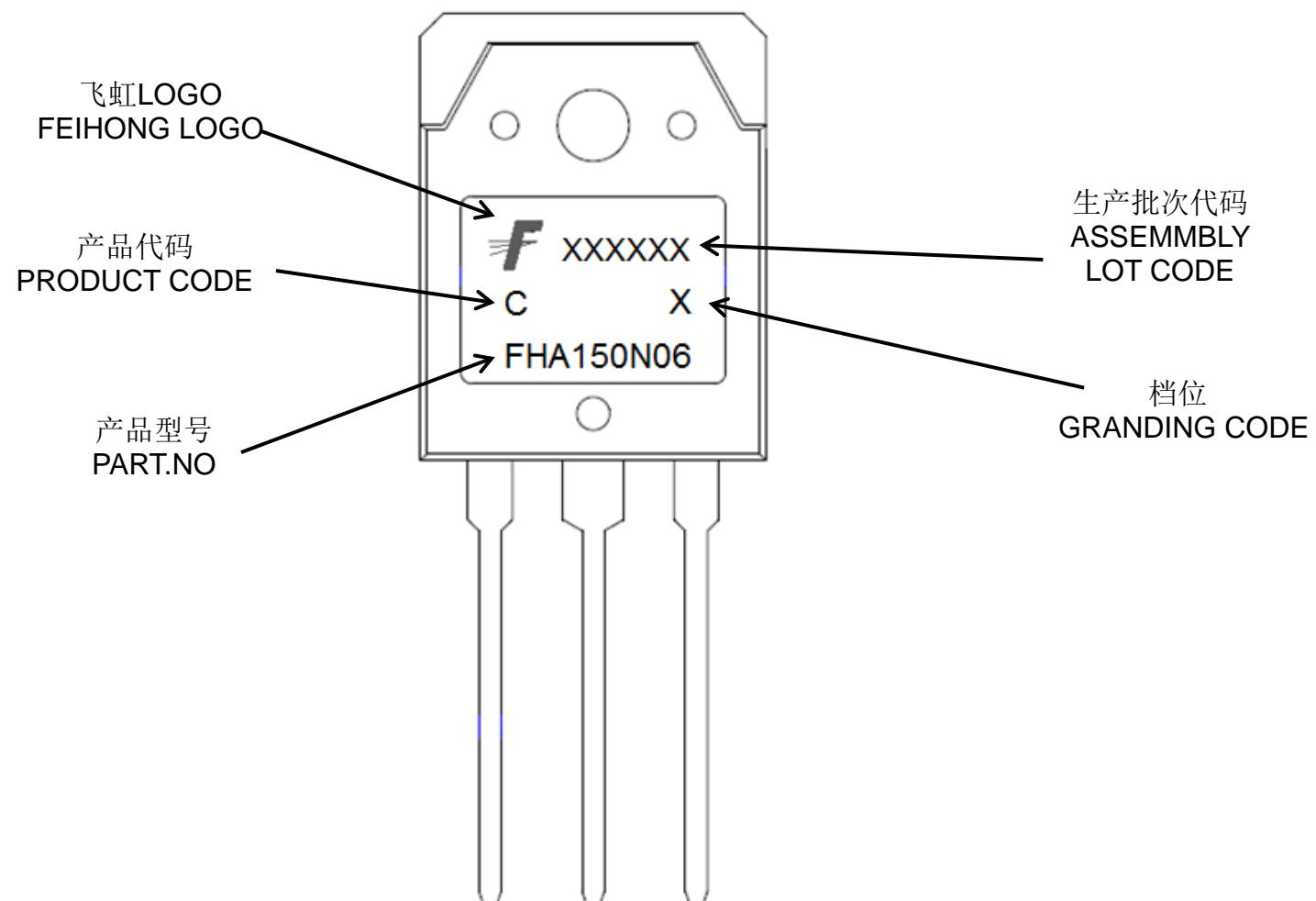


Fig. 13. Maximum Transient Thermal Resistance



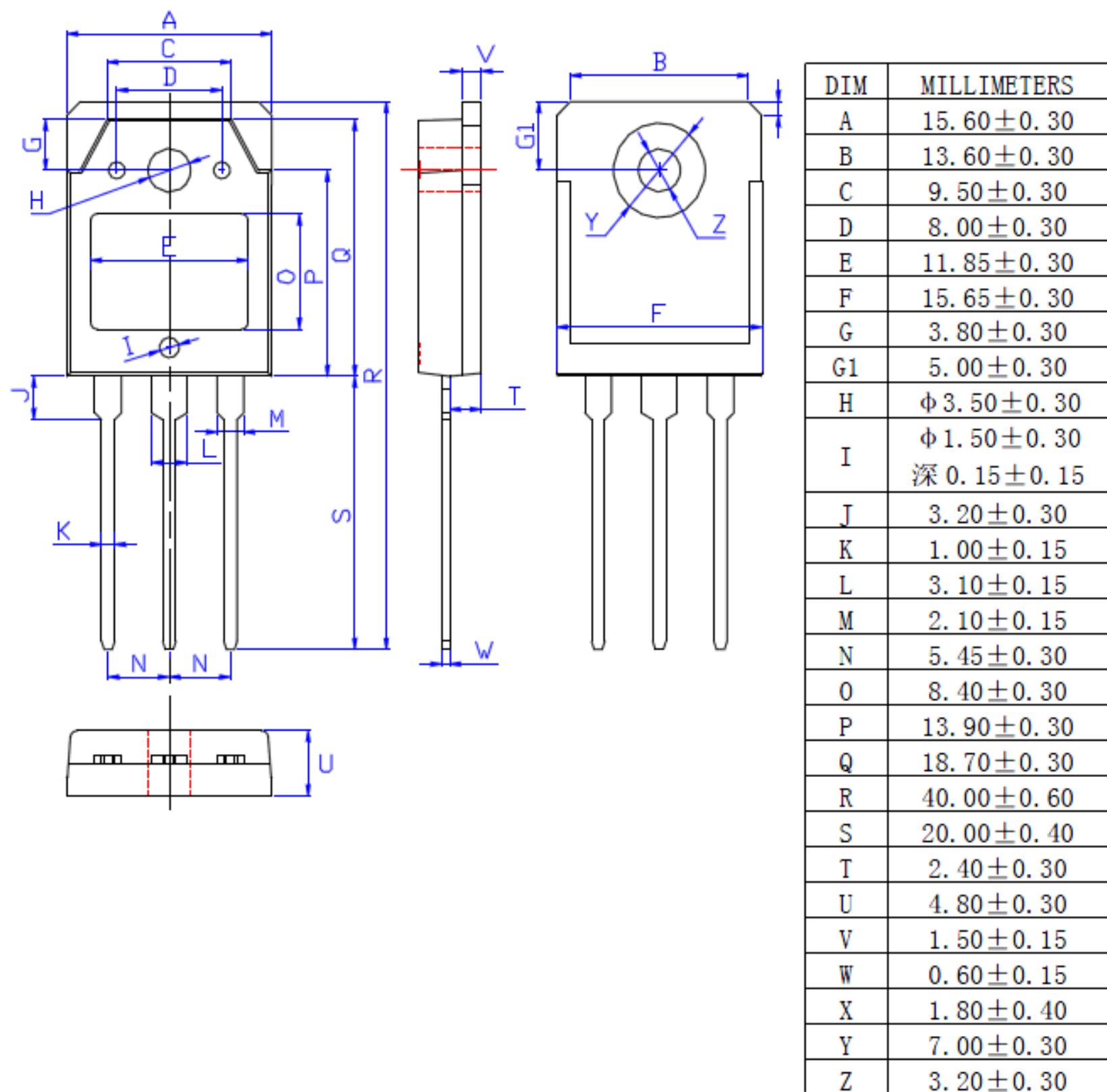
印记 Marking:



外形尺寸：

Package Dimension:

TO-3PN



(Unit: mm)

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